# **DATA SHEET**

## **General Description**

The IDT8N3PF10VA-159I is a programmable LVPECL synthesizer that is "forward" footprint compatible with standard 5mm x 7mm oscillators. The device uses IDT's fourth generation FemtoClock® NG technology for an optimum of high clock frequency and low phase noise performance. Forward footprint compatibility means that a board designed to accommodate the crystal oscillator interface and the optional control pins is also fully compatible with a canned oscillator footprint - the canned oscillator will drop onto the 10-VFQFN footprint for second sourcing purposes. This capability provides designers with programability and lead time advantages of silicon/crystal based solutions while maintaining compatibility with industry standard 5mm x 7mm oscillator footprints for ease of supply chain management.

The IDT8N3PF10VA-159I generates four default frequencies 100MHz or 156.25MHz from a 25MHz fundamental mode crystal, or 212.5MHz or 106.25MHz from a 26.5625MHz fundamental mode crystal. The output frequency is selected by FSEL0 and FSEL1 pins.

### **Features**

- **ï** Fourth Generation FemtoClock® NG technology
- **ï** Footprint compatible with 5mm x 7mm differential oscillators
- **ï** Generates 100MHz or 156.25MHz from a 25MHz crystal, or 212.5MHz or 106.25MHz from a 26.5625MHz mode crystal
- **ï** One differential LVPECL output pair
- **ï** Crystal oscillator interface which can also be overdriven using a single-ended reference clock
- **ï** RMS phase jitter @ 156.25MHz, 10kHz 1MHz: 0.201ps (typical)
- **ï** Full 3.3V or 2.5V operating supply
- **ï** -40°C to 85°C ambient operating temperature
- **ï** Available in lead-free (RoHS 6) package

# **Block Diagram**



# **Pin Assignment**



**10-Lead VFQFN 5mm x 7mm x 1mm package body ePAD size: 1.70mm x 3.70mm NR Package Top View**

5



 $8$  V<sub>CC</sub> Power **Power** Power power supply pin.

# **Table 1. Pin Descriptions**

NOTE: Pullup refers to internal input resistor. See Table 2, Pin Characteristics, for typical values. Table 3. LVCMOS/LVTTL interface levels

clock.

6, 7 | Q, nQ Output Differential output pair. LVPECL interface levels.

## **Table 2. Pin Characteristics**



9 FSEL0 Input Pullup Unter control inputs. Sets the output divider value to one of four values. See Table 3. LVCMOS/LVTTL interface levels.

10 FSEL1 Input Pullup Output divider control inputs. Sets the output divider value to one of four values. See

# **Function Table**

#### **Table 3. Divider Function Table**



# **Absolute Maximum Ratings**

NOTE: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These ratings are stress specifications only. Functional operation of product at these conditions or any conditions beyond those listed in the DC Characteristics or AC Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect product reliability.



# **DC Electrical Characteristics**

**Table 4A. Power Supply DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = -40^{\circ}C$  to 85°C







#### **Table 4C. LVCMOS/LVTTL DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = -40\degree$ C to  $85\degree$ C





#### **Table 4D. LVPECL DC Characteristics,**  $V_{CC} = 3.3V \pm 5\%$  or  $2.5V \pm 5\%$ ,  $V_{EE} = 0V$ ,  $T_A = -40\degree$ C to 85 $\degree$ C

NOTE 1: Outputs terminated with 50 $\Omega$  to V<sub>CC</sub> – 2V.

#### **Table 5. Crystal Characteristics**



## **AC Electrical Characteristics**

**Table 6. AC Characteristics,**  $V_{CC} = 3.3V \pm 5%$  or  $2.5V \pm 5%$ ,  $V_{EE} = 0V$ ,  $T_A = -40°C$  to  $85°C$ 



NOTE: Electrical parameters are guaranteed over the specified ambient operating temperature range, which is established when the device is mounted in a test socket with maintained transverse airflow greater than 500 lfpm. The device will meet specifications after thermal equilibrium has been reached under these conditions.

NOTE: Characterized using a 25MHz, 12pF resonant crystal.

NOTE 1: Please refer to the Phase Noise plots.

NOTE 2: This parameter is defined in accordance with JEDEC Standard 65.

# **Parameter Measurement Information**



**3.3V LVPECL Output Load Test Circuit**



**RMS Phase Jitter**



**Output Rise/Fall Time**



**2.5V LVPECL Output Load Test Circuit**



**Cycle-to-Cycle Jitter**



**Output Duty Cycle/Pulse Width/Period**

Noise PowerdBc / Hz

Noise PowerdBc / Hz

# **Phase Jitter Plot at 156.25MHz (3.3V)**



Offset Frequency (Hz)

# **Applications Information**

## **Overdriving the XTAL Interface**

The XTAL\_IN input can be overdriven by an LVCMOS driver or by one side of a differential driver through an AC coupling capacitor. The XTAL\_OUT pin can be left floating. The amplitude of the input signal should be between 500mV and 1.8V and the slew rate should not be less than 0.2V/nS. For 3.3V LVCMOS inputs, the amplitude must be reduced from full swing to at least half the swing in order to prevent signal interference with the power rail and to reduce internal noise. Figure 1A shows an example of the interface diagram for a high speed 3.3V LVCMOS driver. This configuration requires that the sum of the output impedance of the driver (Ro) and the series resistance (Rs) equals the transmission line impedance. In addition, matched termination at the crystal input will attenuate the signal in half. This

can be done in one of two ways. First, R1 and R2 in parallel should equal the transmission line impedance. For most  $50\Omega$  applications, R1 and R2 can be 100 $\Omega$ . This can also be accomplished by removing R1 and changing R2 to 50 $\Omega$ . The values of the resistors can be increased to reduce the loading for a slower and weaker LVCMOS driver. Figure 1B shows an example of the interface diagram for an LVPECL driver. This is a standard LVPECL termination with one side of the driver feeding the XTAL\_IN input. It is recommended that all components in the schematics be placed in the layout. Though some components might not be used, they can be utilized for debugging purposes. The datasheet specifications are characterized and guaranteed by using a quartz crystal as the input.



**Figure 1A. General Diagram for LVCMOS Driver to XTAL Input Interface**



**Figure 1B. General Diagram for LVPECL Driver to XTAL Input Interface**

### **Recommendations for Unused Input Pins**

#### **Inputs:**

#### **LVCMOS Control Pins**

All control pins have internal pullups; additional resistance is not required but can be added for additional protection. A 1kΩ resistor can be used.

## **Termination for 3.3V LVPECL Outputs**

The clock layout topology shown below is a typical termination for LVPECL outputs. The two different layouts mentioned are recommended only as guidelines.

The differential outputs are low impedance follower outputs that generate ECL/LVPECL compatible outputs. Therefore, terminating resistors (DC current path to ground) or current sources must be used for functionality. These outputs are designed to drive 50Ω



**Figure 2A. 3.3V LVPECL Output Termination Figure 2B. 3.3V LVPECL Output Termination**

transmission lines. Matched impedance techniques should be used to maximize operating frequency and minimize signal distortion. Figures 2A and 2B show two different layouts which are recommended only as guidelines. Other suitable clock layouts may exist and it would be recommended that the board designers simulate to guarantee compatibility across all printed circuit and clock component process variations.



# **Termination for 2.5V LVPECL Outputs**

Figure 3A and Figure 3B show examples of termination for 2.5V LVPECL driver. These terminations are equivalent to terminating 50Ω to  $V_{CC}$  – 2V. For  $V_{CC}$  = 2.5V, the  $V_{CC}$  – 2V is very close to ground



**Figure 3A. 2.5V LVPECL Driver Termination Example**



**Figure 3C. 2.5V LVPECL Driver Termination Example**

level. The R3 in Figure 3B can be eliminated and the termination is shown in Figure 3C.



**Figure 3B. 2.5V LVPECL Driver Termination Example**

## **VFQFN EPAD Thermal Release Path**

In order to maximize both the removal of heat from the package and the electrical performance, a land pattern must be incorporated on the Printed Circuit Board (PCB) within the footprint of the package corresponding to the exposed metal pad or exposed heat slug on the package, as shown in Figure 4. The solderable area on the PCB, as defined by the solder mask, should be at least the same size/shape as the exposed pad/slug area on the package to maximize the thermal/electrical performance. Sufficient clearance should be designed on the PCB between the outer edges of the land pattern and the inner edges of pad pattern for the leads to avoid any shorts.

While the land pattern on the PCB provides a means of heat transfer and electrical grounding from the package to the board through a solder joint, thermal vias are necessary to effectively conduct from the surface of the PCB to the ground plane(s). The land pattern must be connected to ground through these vias. The vias act as "heat pipes". The number of vias (i.e. "heat pipes") are application specific

and dependent upon the package power dissipation as well as electrical conductivity requirements. Thus, thermal and electrical analysis and/or testing are recommended to determine the minimum number needed. Maximum thermal and electrical performance is achieved when an array of vias is incorporated in the land pattern. It is recommended to use as many vias connected to ground as possible. It is also recommended that the via diameter should be 12 to 13mils (0.30 to 0.33mm) with 1oz copper via barrel plating. This is desirable to avoid any solder wicking inside the via during the soldering process which may result in voids in solder between the exposed pad/slug and the thermal land. Precautions should be taken to eliminate any solder voids between the exposed heat slug and the land pattern. Note: These recommendations are to be used as a guideline only. For further information, please refer to the Application Note on the Surface Mount Assembly of Amkor's Thermally/ Electrically Enhance Leadframe Base Package, Amkor Technology.



**Figure 4. P.C. Assembly for Exposed Pad Thermal Release Path – Side View (drawing not to scale)**

## **Schematic Layout**

Figure 5 (next page) shows an example of IDT8N3PF10VA-159I application schematic in which the device is operated at  $V_{CC} = 3.3V$ . The schematic example focuses on functional connections and is intended as an example only and may not represent the exact user configuration. Refer to the pin description and functional tables in the datasheet to ensure the logic control inputs are properly set. For example OE, FSET0 and FSEL1 can be configured from an FPGA instead of pull up and pull down resistors as shown.

There are two LVPECL termination options shown; the simple three resistor termination of R5, R6 and R7 and an AC termination, used when coupling the IDT8N3PF10VA-159I LVPECL output stage to a different logic family receiver. Note that the pull down resistors R8 and R9 that bias the LVPECL output stage are to be placed on the IDT8N3PF10VA-159I side of the PCB directly adjacent to pins 6 and 7 for best signal integrity. Most often each output of a 3.3V LVPECL driver will be DC terminated with a 130 $\Omega$  pull up and an 82 ohm pull down resistor at the 3.3V LVPECL receiver. This is also a valid option with the IDT8N3PF10VA-159I, though the three resistor termination is simpler in regard to component count and layout as well as lower in power dissipation.

NOTE: This device package has an ePAD that is connected to ground internally. Though not necessary, the ePAD should be connected to

GND on the PCB through vias in order to improve heat dissipation. If not connected, the area below the ePAD must be treated as a keep-out region.

As with any high speed analog circuitry, the power supply pins are vulnerable to random noise, so to achieve optimum jitter performance isolation of the  $V_{CC}$  pin from power supply is required. In order to achieve the best possible filtering, it is recommended that the placement of the filter components be on the device side of the PCB as close to the power pins as possible. If space is limited, the 0.1uF capacitor on the  $V_{CC}$  pin must be placed on the device side with direct return to the ground plane though vias. The remaining filter components can be on the opposite side of the PCB.

Power supply filter component recommendations are a general guideline to be used for reducing external noise from coupling into the devices. The filter performance is designed for a wide range of noise frequencies. This low-pass filter starts to attenuate noise at approximately 10kHz. If a specific frequency noise component is known, such as switching power supplies frequencies, it is recommended that component values be adjusted and if required, additional filtering be added. Additionally, good general design practices for power plane voltage stability suggests adding bulk capacitance in the local area of all devices.

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**Figure 5. IDT8N3PF10VA-159I Application Schematic**

# **Power Considerations**

This section provides information on power dissipation and junction temperature for the IDT8N3PF10VA-159I. Equations and example calculations are also provided.

#### **1. Power Dissipation.**

The total power dissipation for the IDT8N3PF10VA-159I is the sum of the core power plus the power dissipation in the load(s). The following is the power dissipation for  $V_{CC} = 3.3V + 5\% = 3.465V$ , which gives worst case results.

NOTE: Please refer to Section 3 for details on calculating power dissipation in the load.

- Power (core)<sub>MAX</sub> =  $V_{\text{CC\_MAX}}$  \*  $I_{\text{EE\_MAX}}$  = 3.465V \* 140mA = 485.1mW
- Power (outputs)<sub>MAX</sub> = 32mW/Loaded Output pair

**Total Power**<sub> $-MAX$ </sub> (3.465V, with all outputs switching) = 485.1mW + 32mW = 517.1mW

#### **2. Junction Temperature.**

Junction temperature, Tj, is the temperature at the junction of the bond wire and bond pad, and directly affects the reliability of the device. The maximum recommended junction temperature is 125°C. Limiting the internal transistor junction temperature, Tj, to 125°C ensures that the bond wire and bond pad temperature remains below 125°C.

The equation for Tj is as follows: Tj =  $\theta_{JA}$  \* Pd\_total + T<sub>A</sub>

 $Tj$  = Junction Temperature

 $\theta_{JA}$  = Junction-to-Ambient Thermal Resistance

Pd\_total = Total Device Power Dissipation (example calculation is in section 1 above)

 $T_A$  = Ambient Temperature

In order to calculate junction temperature, the appropriate junction-to-ambient thermal resistance  $\theta_{JA}$  must be used. Assuming no air flow and a multi-layer board, the appropriate value is 36.8°C/W per Table 7 below.

Therefore, T<sub>i</sub> for an ambient temperature of 85°C with all outputs switching is:

 $85^{\circ}$ C + 0.517W  $*$  36.8 $^{\circ}$ C/W = 104 $^{\circ}$ C. This is below the limit of 125 $^{\circ}$ C.

This calculation is only an example. Tj will obviously vary depending on the number of loaded outputs, supply voltage, air flow and the type of board (multi-layer).

#### **Table 7. Thermal Resistance** θJA **for 10 Lead VFQFN, Forced Convection**



#### **3. Calculations and Equations.**

The purpose of this section is to calculate the power dissipation for the LVPECL output pair.

The LVPECL output driver circuit and termination are shown in Figure 6.



**Figure 6. LVPECL Driver Circuit and Termination**

To calculate power dissipation per output pair due to loading, use the following equations which assume a 50Ω load, and a termination voltage of  $V_{CC}$  – 2V.

- For logic high,  $V_{\text{OUT}} = V_{\text{OH\_MAX}} = V_{\text{CC\_MAX}} 0.8V$  $(V_{CC~MAX} - V_{OH~MAX}) = 0.\overline{8}V$
- $\bullet$  For logic low,  $\mathsf{V}_{\mathsf{OUT}}$  =  $\mathsf{V}_{\mathsf{OL\_MAX}}$  =  $\mathsf{V}_{\mathsf{CC\_MAX}}$   $-$  **1.6V**  $(V_{\text{CC\_MAX}} - V_{\text{OL\_MAX}}) = 1.6V$

Pd\_H is power dissipation when the output drives high.

Pd\_L is the power dissipation when the output drives low.

Pd\_H = [(V<sub>OH\_MAX</sub> – (V<sub>CC\_MAX</sub> – 2V))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>) = [(2V – (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OH\_MAX</sub>) = [(2V – 0.8V)/50Ω] \* 0.8V = **19.2mW**

Pd\_L = [(V<sub>OL\_MAX</sub> – (V<sub>CC\_MAX</sub> – 2V))/R<sub>L</sub>] \* (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>) = [(2V – (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>))/R<sub>L]</sub> \* (V<sub>CC\_MAX</sub> – V<sub>OL\_MAX</sub>) =  $[(2V – 1.6V)/50 $\Omega$ ] * 1.6V = 12.8mW$ 

Total Power Dissipation per output pair = Pd\_H + Pd\_L = **32mW**



# **Reliability Information**

**Table 8.** θJA **vs. Air Flow Table for a 10 Lead VFQFN** 



### **Transistor Count**

The transistor count for IDT8N3PF10VA-159I is: 47,515





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# **10 Lead VFQFN, NR Suffix Package Outline, continued**





# **10 Lead VFQFN, NR Suffix Package Outline, continued**



# **Ordering Information**

#### **Table 9. Ordering Information**





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